



**mitsubishi
electric**

Changes for the Better

SiC POWER MODULES

for a greener tomorrow



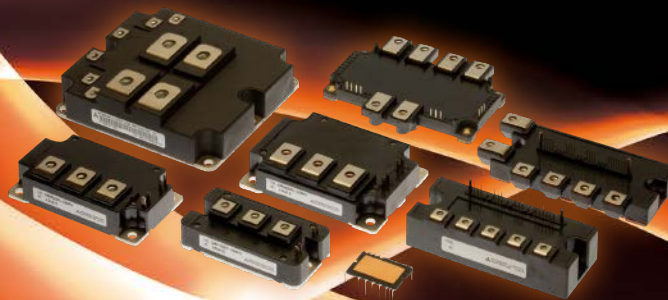
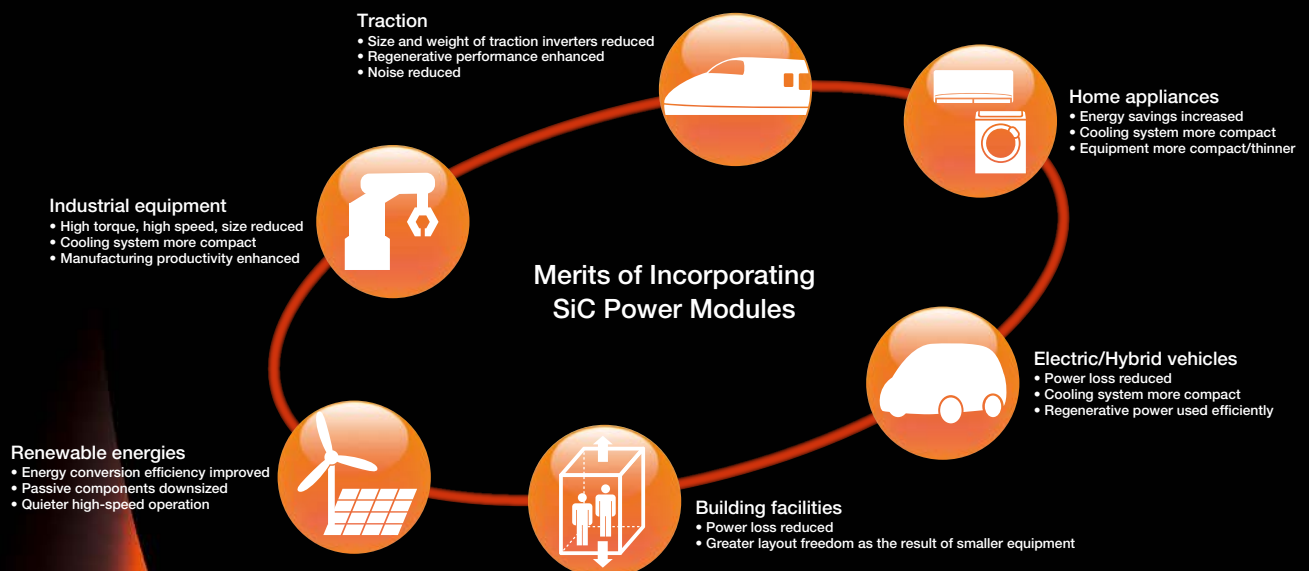
SiC Power Modules

Innovative Power Devices for a Sustainable Future

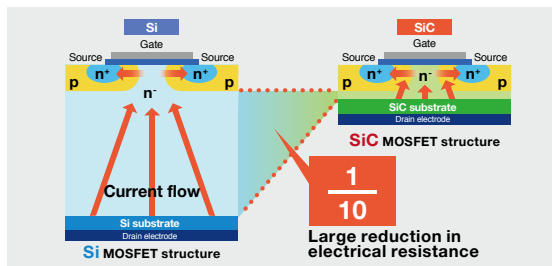
Traction, industrial equipment, building facilities, electric vehicles, renewable energies, home appliances...

Power devices are a key component in power electronics products for contributing to the realization of a low-carbon society. Attracting attention as the most energy-efficient power device is one made using new material, silicon-carbide (SiC). The material characteristics of SiC have led to a dramatic reduction in power loss and significant energy savings for power electronics devices. Mitsubishi Electric began the development of elemental SiC technologies in the early 1990s and has since introduced them to achieve practical energy-saving effects for products manufactured using SiC. Innovative SiC power modules are contributing to the realization of a low-carbon society and more affluent lifestyles.

*SiC: Silicon Carbide-Compound that fuses silicon and carbon at a ratio of one-to-one.

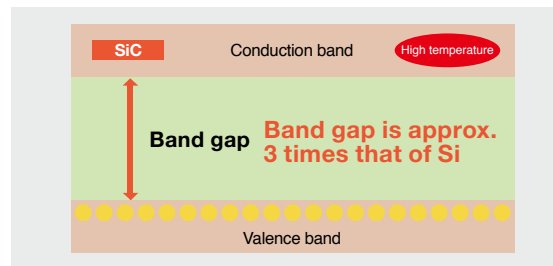


SiC with superior characteristics



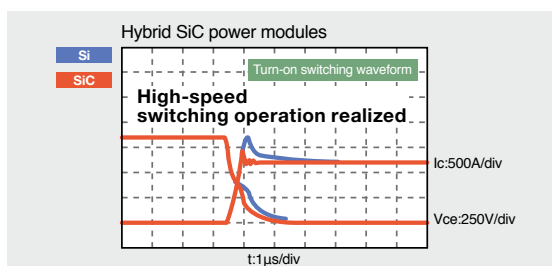
Power loss reduced

SiC has approximately 10 times the critical breakdown strength of silicon. Furthermore, the drift layer that is a main cause of electrical resistance is one-tenth of the thickness. This allows a large reduction in electrical resistance and, in turn, reduces power loss. This SiC characteristic enables dramatic reductions in conductivity loss and switching loss in power devices.



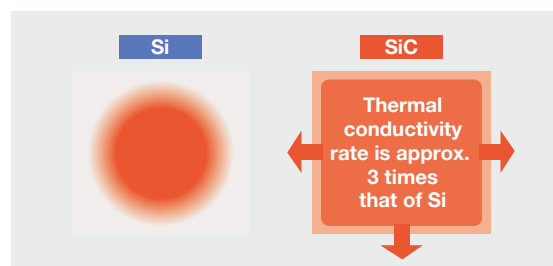
High-temperature operation

When the temperature increases, electrons are excited to the conduction band and the leakage current increases. At times, this results in abnormal operation. However, SiC has three times the band gap width of silicon, preventing the flow of leakage current and enabling operation at high temperatures.



High-speed switching operation

With SiC, owing to the high dielectric breakdown, power loss is reduced and high-voltage is easier to achieve, it is possible to use Schottky Barrier Diodes (SBDs), which cannot be used with Si. SBDs can realize high-speed switching motion because they don't have accumulation carriers. As a result, high-speed switching can be realized.



Heat dissipation

SiC has three times the heat conductivity of silicon, which improves heat dissipation.

SiC power modules appropriated by application

Application	Product name	Model	Rating		Connection	States	Insert pages
			Voltages[V]	Current[A]			
Industrial equipment	Hybrid SiC-IPM	PMH200CS1D060	600	200	6 in 1	Commercially available	P3
		PMH75CL1A120	1200	75	6 in 1	Sample available	
	Full SiC-IPM	PMF75CL1A120				Sample available	
	Full SiC-IPM for PV Applications	PMF75B4L1A060	600	75	4 in 1	Sample available	P4
	Full SiC Power Modules	FMF400BX-24A	1200	400	4 in 1	Commercially available	
		FMF800DX-24A	1200	800	2 in 1	Commercially available	
	Hybrid SiC Power Modules for High-frequency Switching Applications	CMH100DY-24NFH	1200	100	2 in 1	Commercially available	P5
		CMH150DY-24NFH		150			
		CMH200DU-24NFH		200			
		CMH300DU-24NFH		300			
		CMH400DU-24NFH		400			
		CMH600DU-24NFH		600			
Traction	Large Hybrid SiC DIIPM™ for PV Application	PSH50YA2A6	600	50	4 in 1	Commercially available	P6
	Hybrid SiC Power Modules	CMH1200DC-34S	1700	1200	2 in 1	Commercially available	
Home appliances	Super-mini Full SiC DIIPM™	PSF15S92F6	600	15	6 in 1	Commercially available	
	Super-mini Hybrid SiC DIPFPC™	PSH20L91A6-A	600	20Arms	Interleaved	Commercially available	P7
	Super-mini Full SiC DIPFPC™	PSF20L91A6-A				Commercially available	

Terminology

SiCSilicon Carbide
 IPMIntelligent Power Module
 DIIPMDual-In-Line Package Intelligent Power Module
 DIPFPCDual-In-Line Package Power Factor Correction
 SBDSchottky Barrier Diode
 MOSFETMetal Oxide Semiconductor Field Effect Transistor
 IGBTInsulated Gate Bipolar Transistor
 TrTransistor

FWD-SWDiode switching loss
 FWD-DCDiode DC loss
 Tr-SWTransistor switching loss
 Tr-DCTransistor DC loss
 IGBT-SWIGBT switching loss
 IGBT-DCIGBT DC loss
 PVPhotovoltaics
 CSTBTMitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect



600V/200A Hybrid SiC-IPM for Industrial Equipment PMH200CS1D060 **Commercially available**

SiC-SBD incorporated in an IPM with a built-in drive circuit and protection functions

Power loss reduction of approx. 20% contributes to enhancing the performance of industrial machinery

■ Features

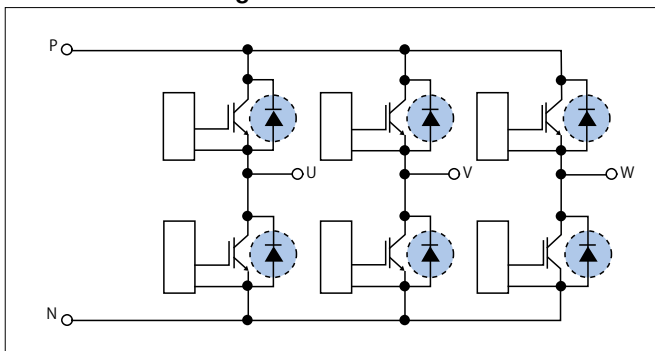
- Hybrid combination of SiC-SBD and IGBT with current and temperature sensors implemented for IPM supplies high functionality and low loss enabling high torque and motor speed
- Recovery loss (Err) reduced by 95% compared to the conventional product*
- Package compatible with the conventional product* making replacement possible

* Conventional product: Mitsubishi Electric S1 Series PM200SC1D060



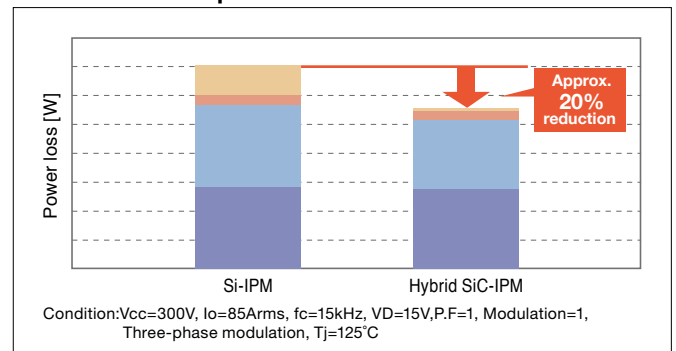
■ Internal circuit diagram

● : SiC-SBD



■ Power loss comparison

■ FWD_SW ■ IGBT_SW
■ FWD_DC ■ IGBT_DC



1200V/75A Hybrid/Full SiC-IPM for Industrial Equipment PMH75CL1A120/PMF75CL1A120 **Sample available**

Built-in drive circuit and protection functions realize high functionality

■ Features

- Incorporates SiC-MOSFET with current sensor and built-in drive circuit and protection functions to deliver high functionality
- Significant reduction in power loss compared to the conventional product*
- Package compatible with the conventional product*

* Conventional product: Mitsubishi Electric IPM L1 Series PM75CL1A120

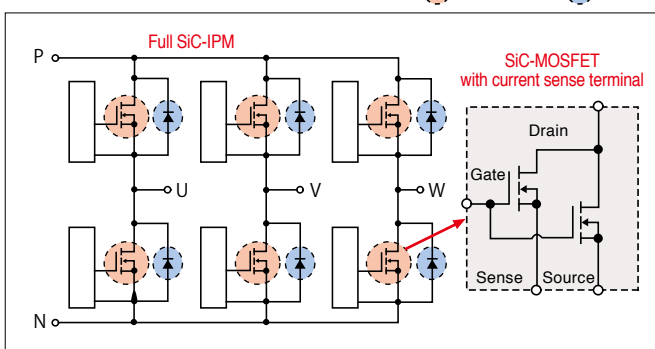
■ Main specifications

Rating	1200V/75A 6in1
Mounted Functions	<ul style="list-style-type: none"> • Built-in drive circuit • Under-voltage protection • Short-circuit protection • Over-temperature protection (Monitoring IGBT chip surface)



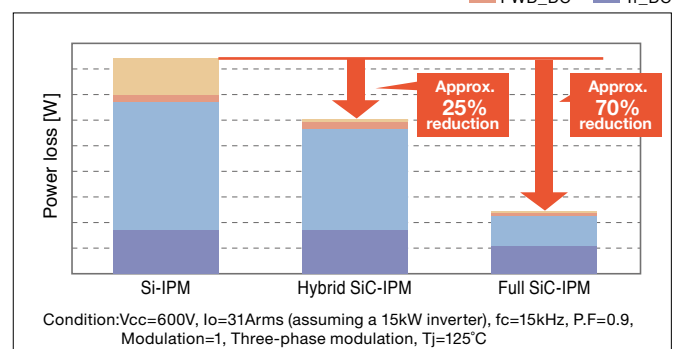
■ Internal circuit diagram

● : SiC-MOSFET ● : SiC-SBD



■ Power loss comparison

■ FWD_SW ■ Tr_SW
■ FWD_DC ■ Tr_DC





600V/75A Full SiC-IPM for PV Applications PMF75B4L1A060

Sample available

**Improved power conversion efficiency
and high-frequency drive enable reactor size to be reduced**

■ Features

- Incorporates SiC-MOSFET with current sensor, built-in drive circuit and protection functions to deliver higher functionality
- Power loss reduced approx. 50% compared to conventional product*
- Improved power conversion efficiency and high-frequency drive enable reactor size to be reduced
- Package compatible with conventional product*

■ Main specifications

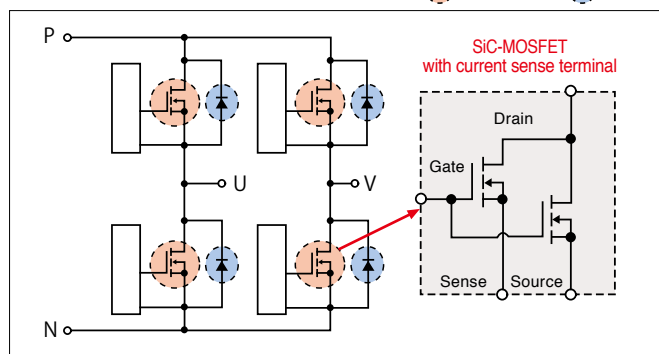
Rating	600V/75A 4-in-1
Functions incorporated	<ul style="list-style-type: none"> • Built-in drive circuit • Under-voltage protection • Short-circuit protection



* Conventional product: Mitsubishi Electric IPM PM75B4LA060

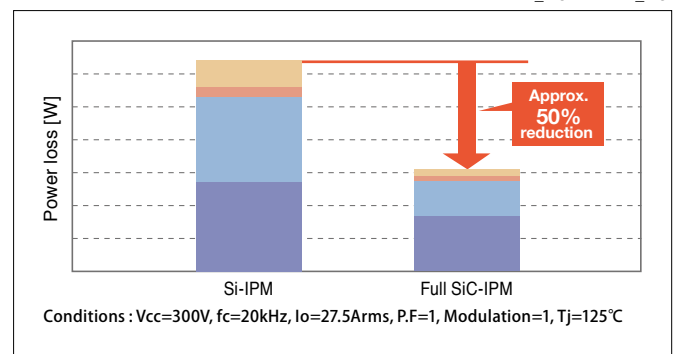
■ Internal circuit diagram

●:SiC-MOSFET ●:SiC-SBD



■ Power loss comparison

FWD_SW Tr_SW
FWD_DC Tr_DC



1200V/400A · 1200V/800A Full SiC Power Modules FMF400BX-24A/FMF800DX-24A

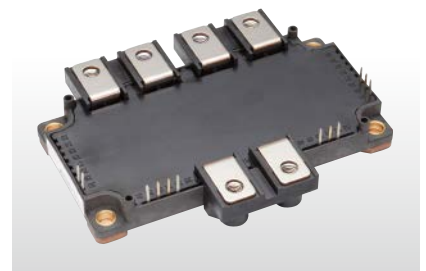
Commercially available

**Contributes to reducing size/weight of industrial-use inverters
with the mounting area reduced by approx. 60%**

■ Features

- Power loss reduced approx. 70% compared to the conventional product*
- Low-inductance package adopted to deliver full SiC performance
- Contributes to realizing smaller/lighter inverter equipment by significantly reducing the package size and realizing a mounting area approx. 60% smaller compared to the conventional product*

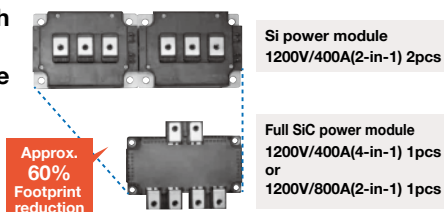
* Conventional product:Mitsubishi Electric CM400DY-24NF(1200V/400A 2in1) 2pcs



■ Product lineup

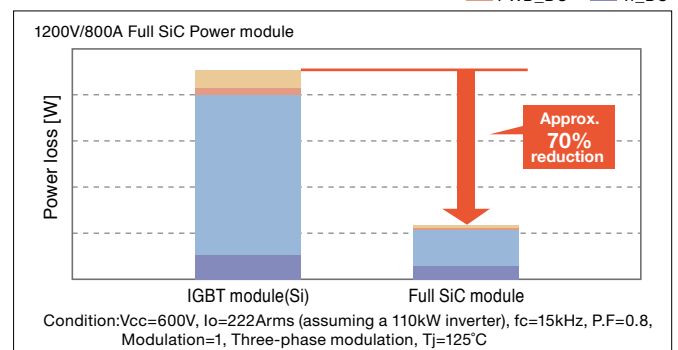
Applications	Rated voltage	Rated current	Circuit configuration	Package size (D x W)
Industrial equipment	1200V	400A	4-in-1	92.3 x 121.7mm
		800A	2-in-1	

■ Comparison with conventional product package



■ Power loss comparison

FWD_SW Tr_SW
FWD_DC Tr_DC





Hybrid SiC Power Modules for High-frequency Switching Applications **Commercially available**

For optimal operation of power electronics devices that conduct high-frequency switching

Features

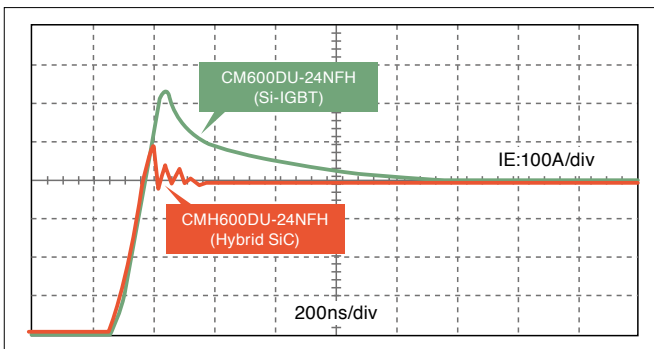
- Power loss reduction of approx. 40% contributes to higher efficiency, smaller size and weight reduction of total system
- Suppresses surge voltage by reducing internal inductance
- Package compatible with the conventional product*
- Conventional product: Mitsubishi Electric NFH Series IGBT Modules

Product lineup

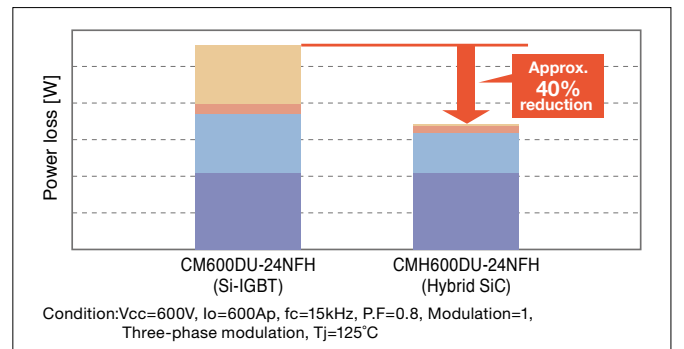
Applications	Model	Rated voltage	Rated current	Circuit configuration	External size (D x W)
Industrial equipment	CMH100DY-24NFH	1200V	100A	2-in-1	48 x 94mm
	CMH150DY-24NFH		150A		48 x 94mm
	CMH200DU-24NFH		200A		62 x 108mm
	CMH300DU-24NFH		300A		62 x 108mm
	CMH400DU-24NFH		400A		80 x 110mm
	CMH600DU-24NFH		600A		80 x 110mm



Recovery waveform (FWD)



Power loss comparison



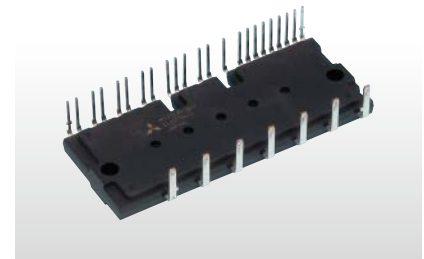
600V/50A Large Hybrid SiC DIIPM™ for PV Applications PSH50YA2A6 **Commercially available**

More efficient power modules for PV power conditioner applications

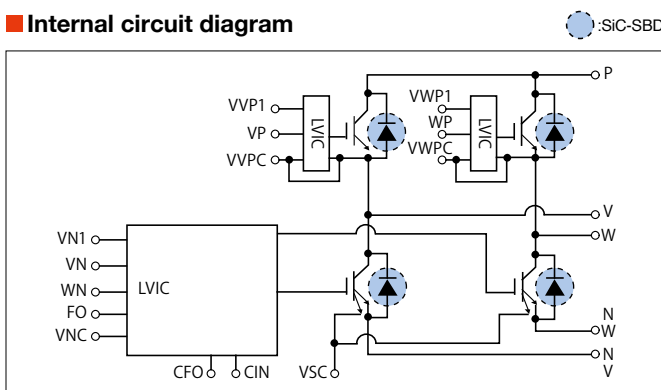
Features

- Hybrid structure achieved with SiC Schottky barrier diode and 7th-generation IGBT chips
- Power loss reduction of approx. 25% compared to the conventional product*
- Helps downsize PV inverter system thanks to modified short-circuit protection scheme

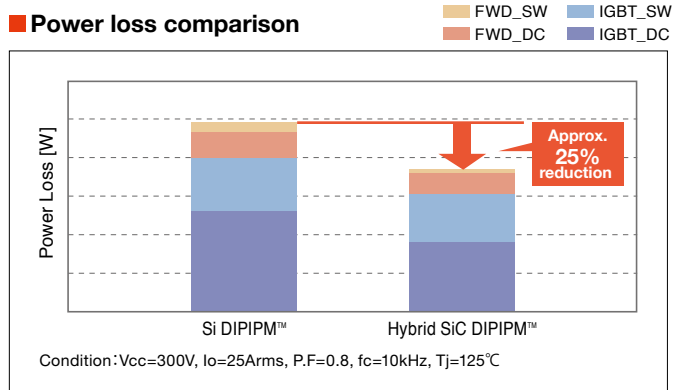
*Conventional product: Mitsubishi Electric Large DIIPM™ PS61A99



Internal circuit diagram



Power loss comparison





1700V/1200A Hybrid SiC Power Modules for Traction Inverters CMH1200DC-34S **Commercially available**

High-power/low-loss/highly reliable modules appropriate for use in traction inverters

■ Features

- Power loss reduced approximately 30% compared to the conventional product*
- Highly reliable design appropriate for use in traction
- Package compatible with the conventional product*

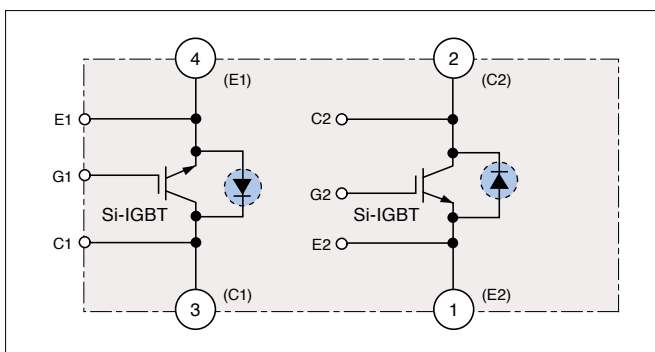
* Conventional product: Mitsubishi Electric Power Module CM1200DC-34N

■ Main specifications

Module	Max. operating temperature	150°C
	Isolation voltage	4000Vrms
Si-IGBT @ 150°C	Collector-emitter saturation voltage	2.3V
	Switching loss 850V/1200V	turn-on 140mJ
		turn-off 390mJ
SiC-SBD @ 150°C	Emitter-collector voltage	2.3V
	Capacitive charge	9.0μC

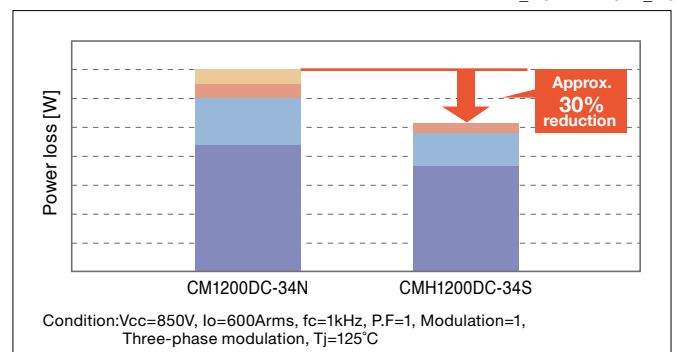


■ Internal circuit diagram



■ Power loss comparison

FWD_SW IGBT_SW
FWD_DC IGBT_DC



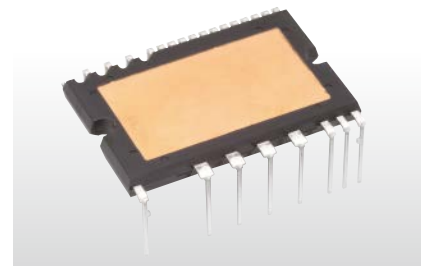
600V/15A Super-mini Full SiC DIPIPM™ for Home Appliances PSF15S92F6 **NEW**

Contributes to extremely high power-efficiency in air conditioners, and easily applicable to industrial equipment

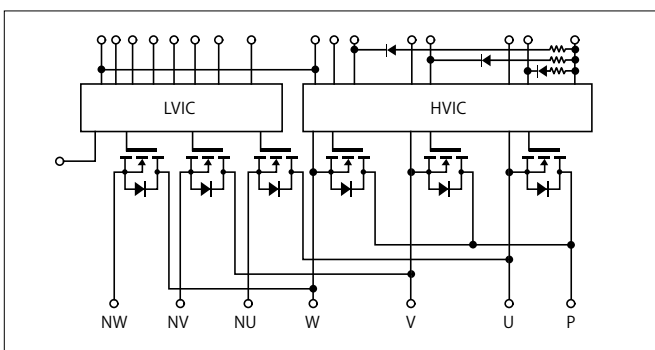
■ Features

- SiC-MOSFET achieves reduction in ON resistance, power loss reduced approx. 70% compared to conventional product*
- Construct low-noise system by reducing recovery current
- Numerous built-in functions: Bootstrap diode for power supply to drive P-side, temperature information output, etc.
- Unnecessary minus-bias gate drive circuit using original high V_{th} SiC-MOSFET technology
- As package and pin layout compatibility with conventional products* is ensured, simply replace with this product to improve performance

* Conventional product: Mitsubishi Electric Super-mini DIPIPM™ Series

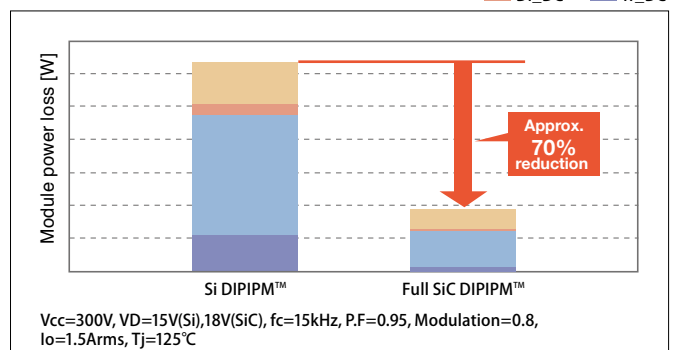


■ Internal block diagram



■ Power loss comparison

Di_SW Tr_SW
Di_DC Tr_DC





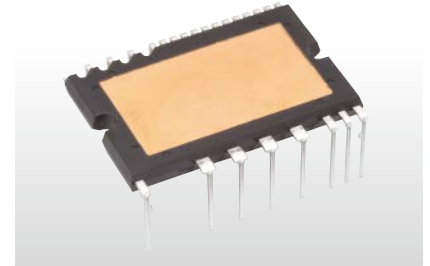
Super-mini Hybrid / Full SiC DIPFPC™ for Home Appliances

PSH20L91A6-A / PSF20L91A6-A **Commercially available**

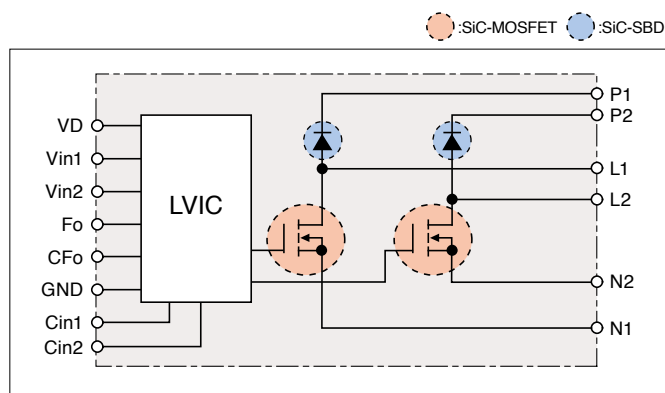
Utilizing SiC enables high-frequency switching and contributes to reducing the size of peripheral components

■ Features

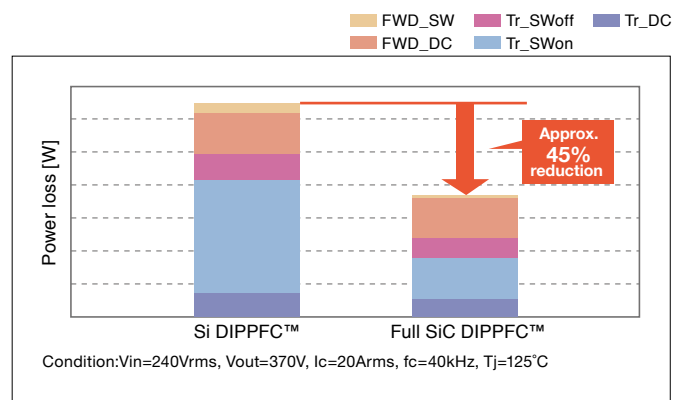
- Incorporating SiC chip in the Super-mini package widely used in home appliances
- The SiC chip allows high-frequency switching (up to 40kHz) and contributes to downsizing the reactor, heat sink and other peripheral components
- Adopts the same package as the Super mini DIPIPM™ to eliminate the need for a spacer between the inverter and heat sink, and to facilitate its implementation



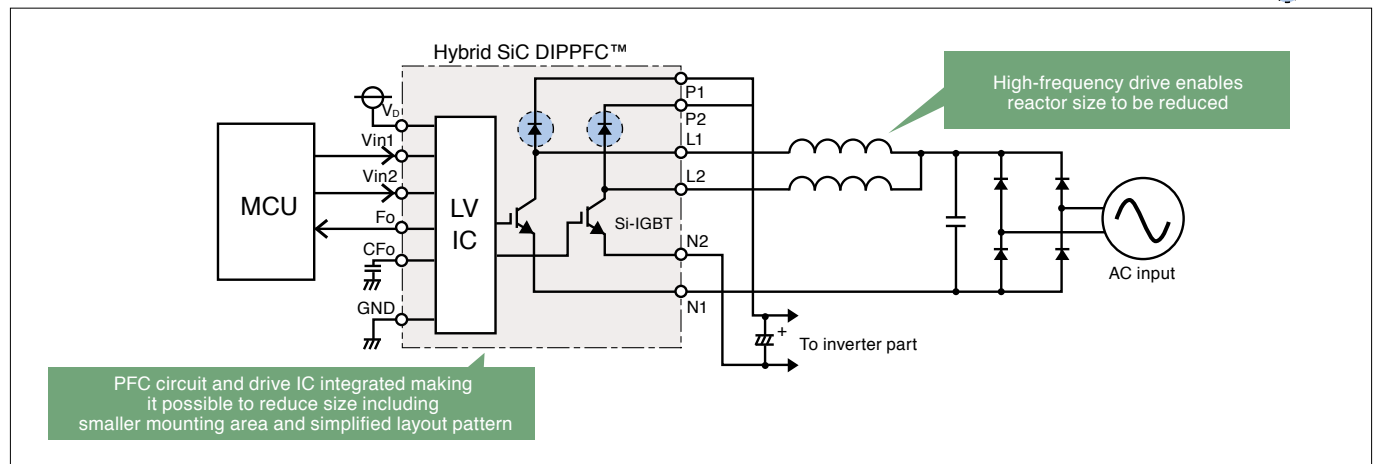
■ Internal block diagram (Full SiC DIPFPC™)



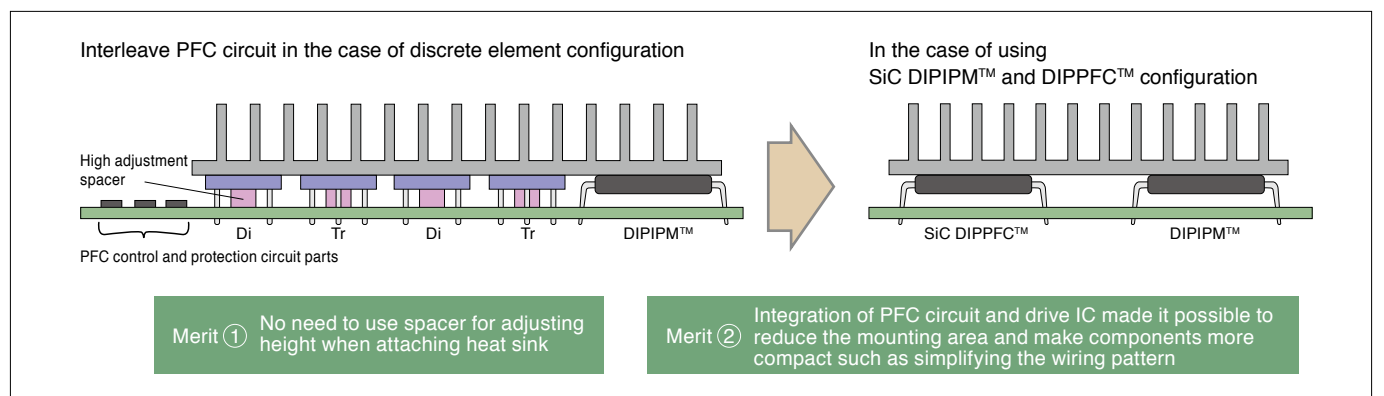
■ Power loss comparison



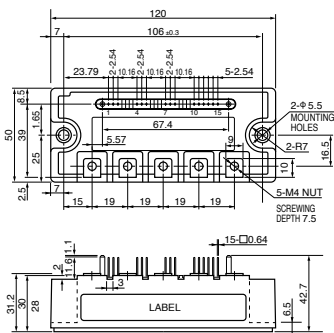
■ Interleaved PFC circuit configuration (for Hybrid SiC DIPFPC™)



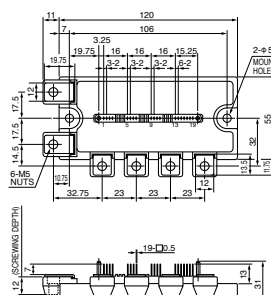
■ Merits of combined use of SiC DIPIPM™ and DIPFPC™



600V/200A Hybrid SiC-IPM
for Industrial Use
PMH200CS1D060

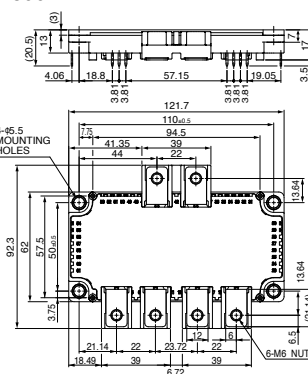


1200V/75A Hybrid/Full SiC-IPM
for Industrial Equipment
PMH75CL1A120/PMF75CL1A120
600V/75A Full SiC-IPM for PV Applications
PMF75B4L1A060

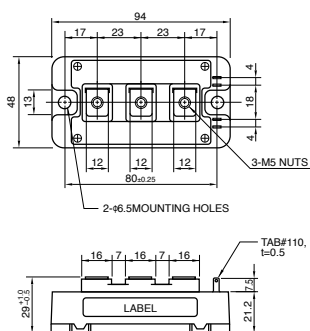


*Tentative No.

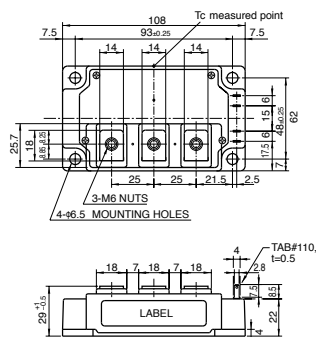
1200V/400A, 1200V/800A
Full SiC Power Modules for Industrial Use
FMF400BX-24A
FMF800DX-24A



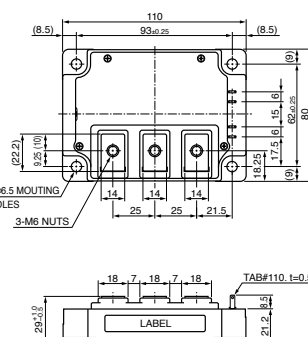
Hybrid SiC Power Modules for
High-frequency Switching Applications
CMH100DY-24NFH
CMH150DY-24NFH



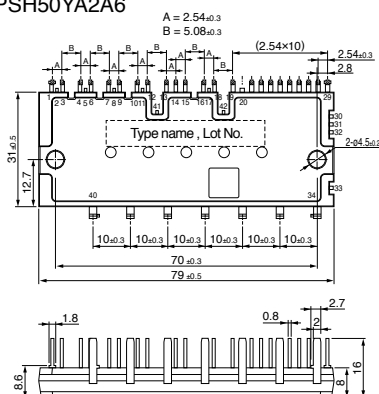
Hybrid SiC Power Modules for
High-frequency Switching Applications
CMH 200DU-24NFH
CMH 300DU-24NFH



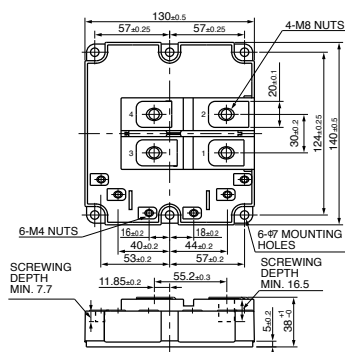
Hybrid SiC Power Modules for
High-frequency Switching Applications
CMH 400DU-24NFH
CMH 600DU-24NFH



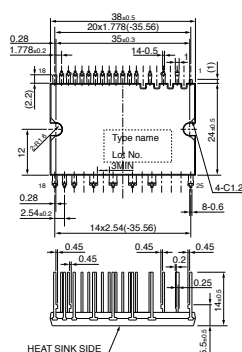
600V/50A Large Hybrid SiC DIPIPM™ for PV Applications PSH50YA2A6



1700V/1200A Hybrid SiC Power Modules
for Traction Inverters
CMH1200DC-34S



600V/15A Super-mini Full SiC DIIPM™
PSF15S92F6-A
Super-mini Hybrid / Full SiC DIPFPC™
PSH20L91A6-A / PSF20L91A6-A
Long



Development of Mitsubishi Electric SiC Power Devices and Power Electronics Equipment Incorporating Them

Mitsubishi Electric began developing SiC as a new material in the early 1990s. Pursuing special characteristics, we succeeded in developing various elemental technologies.

In 2010, we commercialized the first air conditioner in the world equipped with a SiC power device.

Furthermore, substantial energy-saving effects have been achieved for traction and FA machinery.

We will continue to provide competitive SiC power modules with advanced development and achievements from now on.

Early 1990s

Developed new material, silicon-carbide (SiC) power semiconductor, maintaining a lead over other companies

2000s

Developed various elemental technologies

2006

January 2006
Successfully developed SiC inverter for driving motor rated at 3.7kW

2010

January 2010
Developed large-capacity power module equipped with SiC diode



October 2010
Launched "Kirigamine" inverter air conditioner



2011

January 2011
Verified highest power conversion efficiency*1 for solar power generation system power conditioner (domestic industry)



October 2011
Commercialized SiC inverter for use in railcars



2009

February 2009
Verified 11kW SiC inverter, world's highest value*1 with approx. 70% reduction in power loss



November 2009
Verified 20kW SiC inverter, world's highest value*1 with approx. 90% reduction in power loss



2012

March 2012
Developed motor system with built-in SiC inverter*2



September 2012
Verified built-in main circuit system for railcars



**Contributing to the realization
of a low-carbon society and
more affluent lifestyles**

2014

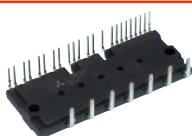
February 2014
Developed EV motor
drive system with
built-in SiC inverter*2



May 2014
**Began shipping samples
of hybrid SiC power modules
for high-frequency
switching applications**



November 2014
**Launched Large Hybrid
SiC DIPIPM™
for PV Applications**



2016

April 2016
**Launched Super-mini
Full SiC DIPIPM™**



May 2016(Tentative)
Launched package
air conditioners with
full SiC DIPIPM™ in Japan



2015

January 2015
Launched power conditioner
for PV equipped
with full SiC-IPM



June 2015
Railcar traction system with
full SiC power modules installed
in Shinkansen bullet trains



2013

July 2012
**Began shipping samples
of hybrid SiC
power modules**



December 2012
Launched CNC drive unit
equipped with SiC power module



February 2013
Developed SiC for
application in elevator
control systems*2



February 2013
Developed technologies
to increase capacities of
SiC power modules*2



March 2013
Delivered auxiliary power
supply systems for railcars



May 2013
**Launched SiC power
modules**



December 2013
Launched railcar traction inverter
with full SiC power module



* 1 Researched in press releases by Mitsubishi Electric. * 2 Currently under development, as of April 2016.

* The year and month listed are based on press releases or information released during the product launch month in Japan.

Please visit our website for further details.

www.MitsubishiElectric.com

Keep safety first in your circuit designs!

- Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
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for a greener tomorrow

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MITSUBISHI ELECTRIC CORPORATION

HEAD OFFICE: TOKYO BLDG., 2-7-3, MARUNOUCHI, CHIYODA-KU, TOKYO 100-8310, JAPAN
www.MitsubishiElectric.com